

Docket: CS 99 - 065  
S/N: 09/442,499



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To: Commissioner of Patents and Trademarks  
Washington, D.C. 20231

From: George O. Saile, Reg. No. 19,572  
20 McIntosh Drive  
Poughkeepsie, N.Y. 12603

Subject:

RECEIVED  
MAR 06 2002  
TC 1700

Serial No.: 09/442,499	Filed: 11/18/99
Inventor: Ho	
Title: Plasma Etch Method For Forming Plasma Etched Silicon Layer	
Group Art Unit: 1763	Examiner: Goudreau, G.
Attorney Docket: CS 99 - 065	

H/C  
3/18/02  
MW

### RESPONSE TO PATENT OFFICE ACTION


Dear Sir:

In response to the office action dated 11/07/01, please consider the following remarks:

### CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner of Patent and Trademarks, Washington, D.C. 20231, on February 1, 2002.

Signature/Date

  
Stephen B. Ackerman, Reg #37,761 2/1/02